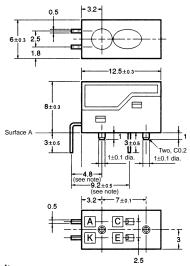
EE-SY169A

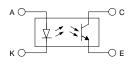
Photomicrosensor (Reflective)

■ Dimensions

Note: All units are in millimeters unless otherwise indicated.



Internal Circuit



Terminal No.	Name	
Α	Anode	
К	Cathode	
С	Collector	
Е	Emitter	

Note: These dimensions are for the surface A. Other lead wire pitch dimensions are for the case surface.

Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.3
3 < mm ≤ 6	±0.375
6 < mm ≤ 10	±0.45
10 < mm ≤ 18	±0.55
18 < mm ≤ 30	±0.65

■ Features

- High-quality model with plastic lenses.
- Highly precise sensing range with a tolerance of ±0.6 mm horizontally and vertically.
- Convergent reflective model with infrared LED.

■ Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Rated value
Emitter	Forward current	I _F	50 mA (see note 1)
	Pulse forward current	I _{FP}	1 A (see note 2)
	Reverse voltage	V_R	3 V
Detector	Collector-Emitter voltage	V_{CEO}	30 V
	Emitter-Collector voltage	V_{ECO}	
	Collector current	I _C	20 mA
	Collector dissipation	P _C	100 mW (see note 1)
Ambient temperature	Operating	Topr	0°C to 70°C
	Storage	Tstg	–20°C to 80°C
Soldering temperature		Tsol	260°C (see note 3)

Note: 1. Refer to the temperature rating chart if the ambient temperature exceeds 25°C.

- 2. The pulse width is 10 μ s maximum with a frequency of 100 Hz.
- 3. Complete soldering within 10 seconds.

■ Electrical and Optical Characteristics (Ta = 25°C)

	Item	Symbol	Value	Condition
Emitter	Forward voltage	V _F	1.5 V max.	I _F = 30 mA
	Reverse current	I _R	10 μA max.	V _R = 4 V
	Peak emission wavelength	λ_{P}	920 nm typ.	I _F = 20 mA
Detector	Light current	IL	160 μA min., 2,000 μA max.	I _F = 20 mA, V _{CE} = 5 V White paper with a reflection ratio of 90%, d = 4 mm (see note)
	Dark current	I _D	2 nA typ., 200 nA max.	V _{CE} = 5 V, 0 ℓx
	Leakage current	I _{LEAK}	2 μA max.	$I_F = 20 \text{ mA}, V_{CE} = 5 \text{ V}$ with no reflection
	Collector–Emitter saturated voltage	V _{CE} (sat)		
	Peak spectral sensitivity wavelength	λ _P	850 nm typ.	V _{CE} = 5 V
Rising time		tr	30 μs typ.	$V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega, I_L = 1 \text{ mA}$
Falling time	•	tf	30 μs typ.	$V_{CC} = 5 \text{ V}, R_{L} = 1 \text{ k}\Omega, I_{L} = 1 \text{ mA}$

Note: The letter "d" indicates the distance between the top surface of the sensor and the sensing object.